# XN04401 (XN4401)

### Silicon PNP epitaxial planar type

For general amplification

#### Features

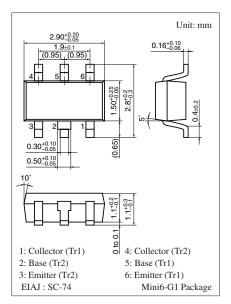
- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• 2SB0709A (2SB709A)  $\times$  2

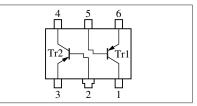
Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-60	V					
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V					
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-7	V					
Collector current	I <sub>C</sub>	-100	mA					
Peak collector current	I <sub>CP</sub>	-200	mA					
Total power dissipation	P <sub>T</sub>	300	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T <sub>stg</sub>	-55 to +150	°C					

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$



#### Marking Symbol: 5K

#### Internal Connection

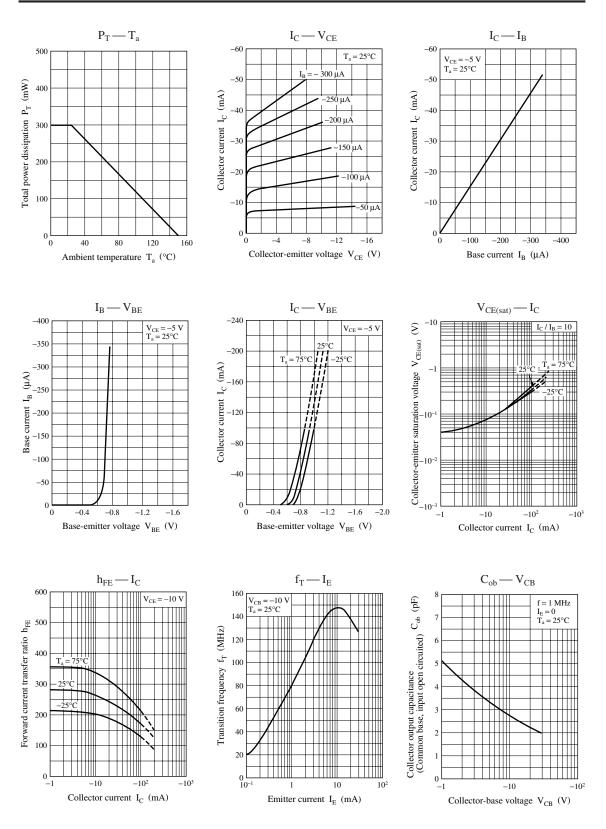


## Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

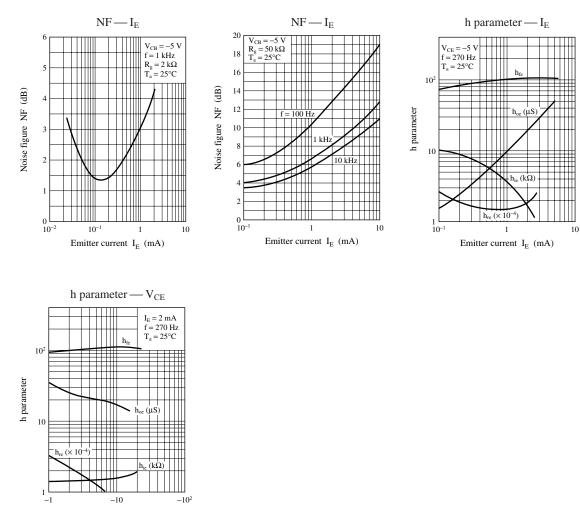
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$	-60			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_E = -10 \ \mu A, \ I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -20 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -10 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = -10 \text{ V}, I_C = -2 \text{ mA}$	160		460	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{C} = -100 \text{ mA}, I_{B} = -10 \text{ mA}$		- 0.3	- 0.5	V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		2.7		pF
(Common base, input open circuited)						

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Note) The part number in the parenthesis shows conventional part number.



## Panasonic



Collector-emitter voltage  $V_{CE}$  (V)

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